

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (previously presented): A floppy disk comprising a base material and, sequentially formed on both surfaces of said base material, a metal seed layer, a primer layer, a magnetic layer, a protective layer, and a lubricant layer,

wherein said base material comprises a nonmagnetic flexible support member with a thickness in the range of 30 - 150  $\mu\text{m}$  and formed on both surfaces of said nonmagnetic flexible support member a heat-resistant macromolecular flattening layer, wherein said heat-resistant macromolecular flattening layer comprises at least one type of silicone resin, polyimide resin, polyamideimide resin or polyamide resin,

wherein the linear expansion coefficient of the seed layer ( $E_{SE}$ ) and the linear expansion coefficient of the primer layer ( $E_{UL}$ ) satisfy a relation of:  $|E_{SE} - E_{UL}| / E_{UL} < 0.3$ , and the tensile strength of the seed layer ( $S_{SE}$ ) and the tensile strength of the primer layer ( $S_{UL}$ ) satisfy a relation of:  $S_{SE} / S_{UL} > 1$ .

2. (canceled).

3. (canceled).

4. (previously presented): A floppy disk according to claim 1, wherein the thickness of the flattening layer is within the range of 0.1 - 5.0  $\mu\text{m}$ .

5. (previously presented): A floppy disk according to claim 1, wherein the thickness of the flexible support member is within the range of 30 - 100  $\mu\text{m}$ .

Claims 6-20. (canceled).

21. (previously presented): A floppy disk according to claim 1, wherein micro-projections comprising fillers are formed on said flattening layer and between said flattening layer and said seed layer.

22. (previously presented): A floppy disk according to claim 4, wherein micro-projections comprising fillers are formed on said flattening layer and between said flattening layer and said seed layer.

23. (previously presented): A floppy disk according to claim 21, wherein said fillers comprise inorganic oxides and have particle size within the range of 5 - 40 nm.

24. (previously presented): A floppy disk according to claim 22, wherein said fillers comprise inorganic oxides and have particle size within the range of 5 - 40 nm.

25. (previously presented): A floppy disk according to claim 23, wherein temperature of the support member during the formation of the metal layer is within the range of 10 - 200°C.

26. (previously presented): A floppy disk according to claim 24, wherein temperature of the support member during the formation of the metal layer is within the range of 10 - 200°C.

27. (previously presented): A floppy disk according to claim 25, wherein the magnetic layer comprises a CoCr alloy as main component.

28. (previously presented): A floppy disk according to claim 26, wherein the magnetic layer comprises a CoCr alloy as main component.

29. (previously presented): A floppy disk according to claim 27, wherein the Cr concentration in the magnetic layer is within the range of 10 - 30 atom %.

30. (previously presented): A floppy disk according to claim 28, wherein the Cr concentration in the magnetic layer is within the range of 10 - 30 atom %.

**AMENDMENT UNDER 37 C.F.R. § 1.111**

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**Q58116**

31. (previously presented): A floppy disk according to claim 29, wherein the primer layer comprises Cr or a nonmagnetic alloy containing Cr as main component, and the Cr content of the primer layer is within the range of 77 - 100 atom %.

32. (previously presented): A floppy disk according to claim 30, wherein the primer layer comprises Cr or a nonmagnetic alloy containing Cr as main component, and the Cr content of the primer layer is within the range of 77 - 100 atom %.

33. (new): A floppy disk according to claim 1, wherein the seed layer contains at least one metal selected from the group consisting of Ta, Mo, W, V, Zr, Cr, Rh, Hf, Nb, Mn, Ni, Al, and Ru, or an alloy of these elements.

34. (new): A floppy disk according to claim 33, wherein the thickness of the seed layer is in the range of 20-60 nm.